



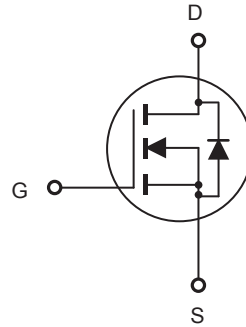
CED02N65A/CEU02N65A

N-Channel Enhancement Mode Field Effect Transistor

PRELIMINARY

FEATURES

- 650V, 1.2A, $R_{DS(ON)} = 10.5\Omega$ @ $V_{GS} = 10V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Lead free product is acquired.
- TO-251 & TO-252 package.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current-Continuous @ $T_C = 25\text{ C}$ @ $T_C = 100\text{ C}$	I_D	1.2	A
		0.8	A
Drain Current-Pulsed ^a	I_{DM}	4.8	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above 25°C	P_D	35.7	W
		0.29	W/ $^\circ\text{C}$
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^\circ\text{C/W}$

This is preliminary information on a new product in development now .
Details are subject to change without notice .

Rev 1. 2011.Oct
<http://www.cetsemi.com>



CED02N65A/CEU02N65A

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 30V, V_{DS} = 0V$			10	μA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -30V, V_{DS} = 0V$			-10	μA
On Characteristics^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.5		4.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5A$		8.5	10.5	Ω
Dynamic Characteristics^c						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{ MHz}$		205		pF
Output Capacitance	C_{oss}			50		pF
Reverse Transfer Capacitance	C_{rss}			20		pF
Switching Characteristics^c						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300V, I_D = 1.2A, V_{GS} = 10V, R_{GEN} = 4.7\Omega$		11	22	ns
Turn-On Rise Time	t_r			10	20	ns
Turn-Off Delay Time	$t_{d(off)}$			16	32	ns
Turn-Off Fall Time	t_f			8	16	ns
Total Gate Charge	Q_g	$V_{DS} = 480V, I_D = 1.2A, V_{GS} = 10V$		6.9	9.1	nC
Gate-Source Charge	Q_{gs}			0.9		nC
Gate-Drain Charge	Q_{gd}			4.6		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current	I_S				1.2	A
Drain-Source Diode Forward Voltage ^b	V_{SD}	$V_{GS} = 0V, I_S = 0.6A$			1.5	V
Notes : □ a.Repetitive Rating : Pulse width limited by maximum junction temperature.□ b.Device Mounted on FR4 Board, $t < 10\text{ sec.}$ □ c.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.□ d.Guaranteed by design, not subject to production testing.□ e.L = 1mH, $I_{AS} = 1.2A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25\text{ C.}$ □						



CED02N65A/CEU02N65A

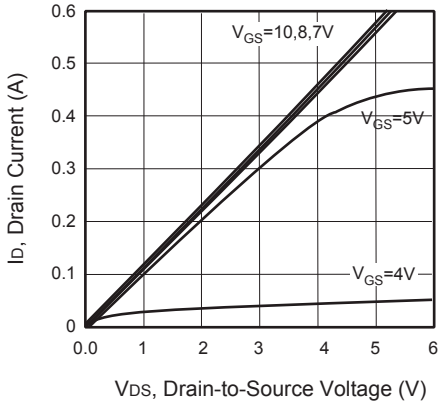


Figure 1. Output Characteristics

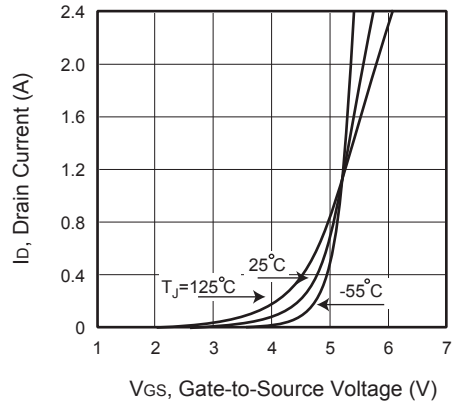


Figure 2. Transfer Characteristics

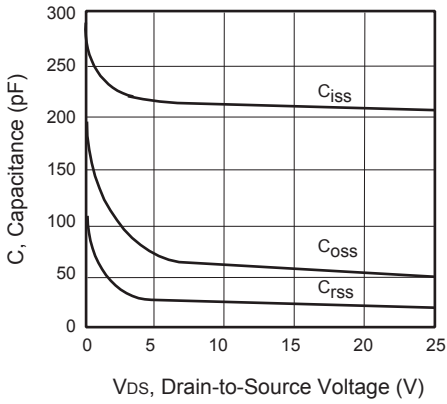


Figure 3. Capacitance

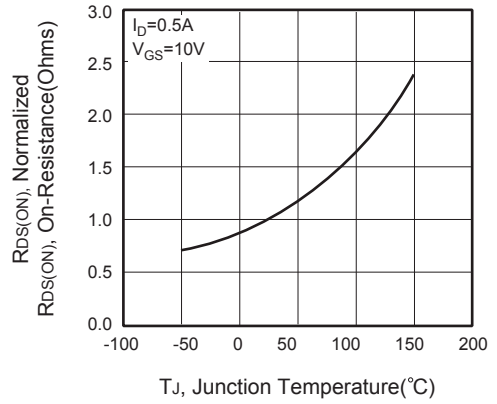


Figure 4. On-Resistance Variation with Temperature

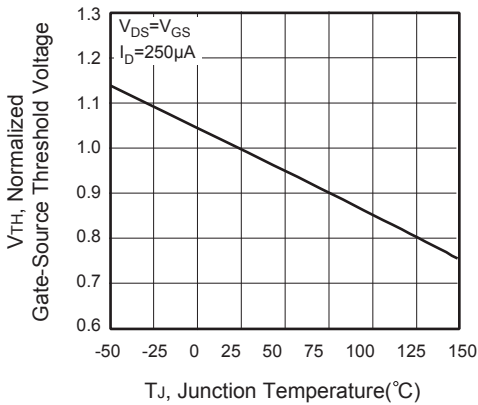


Figure 5. Gate Threshold Variation with Temperature

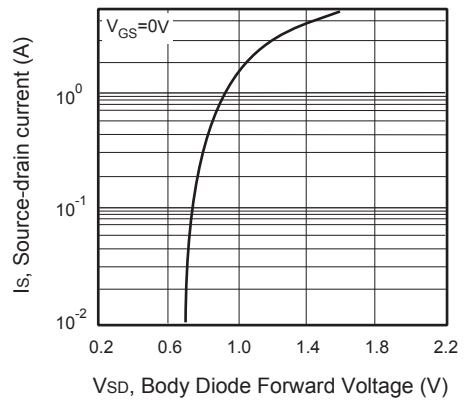


Figure 6. Body Diode Forward Voltage Variation with Source Current



CED02N65A/CEU02N65A

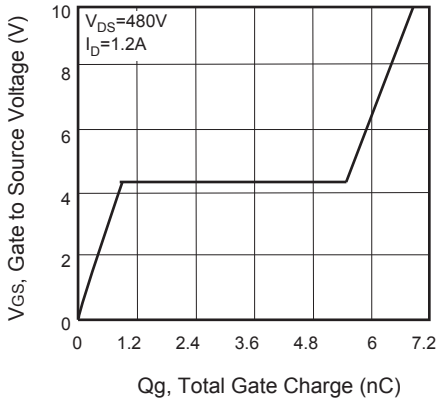


Figure 7. Gate Charge

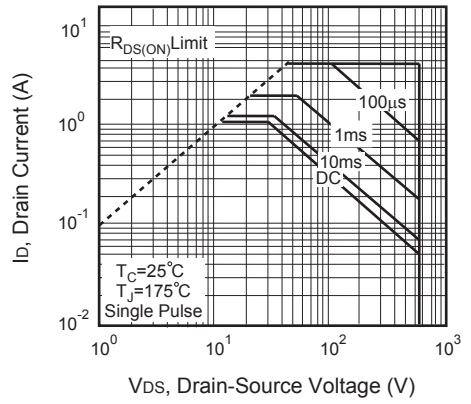


Figure 8. Maximum Safe Operating Area

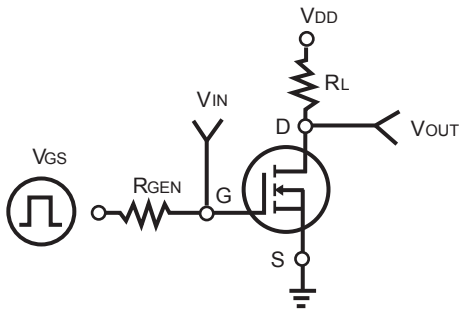


Figure 9. Switching Test Circuit

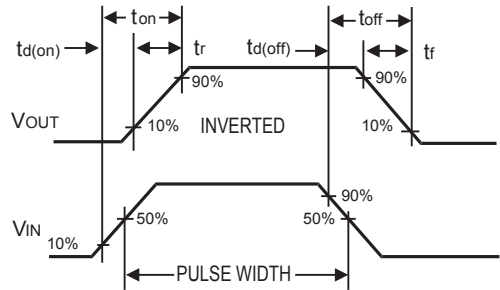


Figure 10. Switching Waveforms

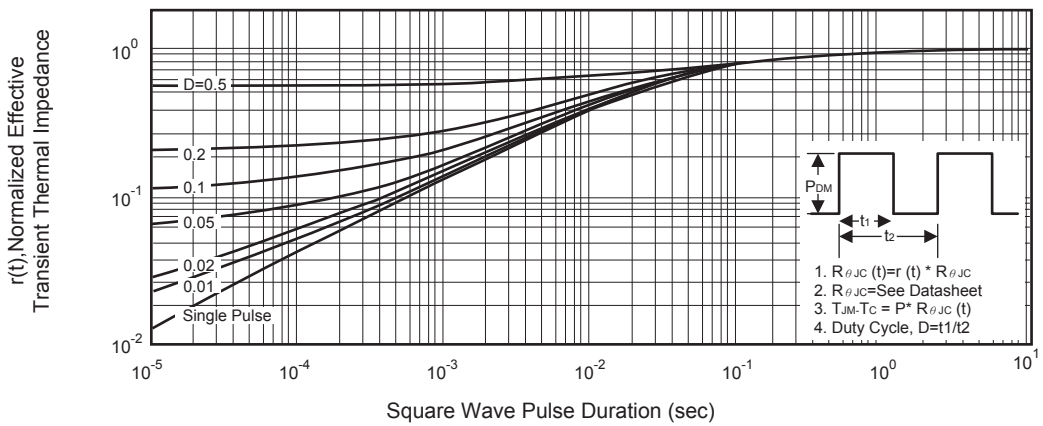


Figure 11. Normalized Thermal Transient Impedance Curve